**Vishay Semiconductors** 



## Hyperfast Rectifier, 4 A FRED Pt®



DPAK (TO-252AA)

Circuit configuration

PRIM

IARY CHARACTERISTICS							
I <sub>F(AV)</sub>	4 A						
V <sub>R</sub>	200 V						
V <sub>F</sub> at I <sub>F</sub>	0.71 V						
1 (1	00						

t<sub>rr</sub> (typ.) 23 ns 175 °C T<sub>.1</sub> max. DPAK (TO-252AA) Package

Single

#### **FEATURES**

- · Hyperfast recovery time
- 175 °C max. operating junction temperature
- Output rectification freewheeling
- Low forward voltage drop reduced Q<sub>rr</sub> and soft recovery
- Low leakage current
- AEC-Q101 qualified
- · Meets JESD 201 class 2 whisker test
- Meets MSL level 1, per J-STD-020, LF maximum peak of 260 °C
- Material categorization: for definitions of compliance please see www.vishay.com/doc?99912

#### **DESCRIPTION / APPLICATIONS**

State of the art hyperfast recovery rectifiers specifically designed with optimized performance of forward voltage drop and hyperfast recovery time.

The planar structure and the platinum doped life time control guarantee the best overall performance, ruggedness and reliability characteristics.

These devices are intended for use in the output rectification stage of SMPS, UPS, DC/DC converters as well as freewheeling diode in low voltage inverters and chopper motor drives.

Their extremely optimized stored charge and low recovery current minimize the switching losses and reduce over dissipation in the switching element and snubbers.

ABSOLUTE MAXIMUM RATINGS				
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS
Peak repetitive reverse voltage	V <sub>RRM</sub>		200	V
Average rectified forward current	I <sub>F(AV)</sub>	T <sub>C</sub> = 164 °C	4	
Non-repetitive peak surge current	I <sub>FSM</sub>	T <sub>J</sub> = 25 °C	80	А
Peak repetitive forward current	I <sub>FM</sub>	$T_{C}$ = 164 °C, f = 20 kHz, d = 50 %	8	
Operating junction and storage temperatures	T <sub>J</sub> , T <sub>Stg</sub>		-65 to +175	°C

<b>ELECTRICAL SPECIFICATIONS</b> (T <sub>J</sub> = 25 °C unless otherwise specified)							
PARAMETER	SYMBOL	TEST CONDITIONS		TYP.	MAX.	UNITS	
Breakdown voltage, blocking voltage	V <sub>BR</sub> , V <sub>R</sub>	I <sub>R</sub> = 100 μA	200	-	-		
Forward voltage	Ň	I <sub>F</sub> = 4 A	-	0.87	0.95	V	
Forward voltage V <sub>F</sub>	I <sub>F</sub> = 4 A, T <sub>J</sub> = 150 °C	-	0.71	0.80			
Poverse leakage ourrent	1	$V_R = V_R$ rated	-	-	3		
Reverse leakage current I <sub>R</sub>		$T_J = 150 \text{ °C}, V_R = V_R \text{ rated}$	-	2	20	μA	
Junction capacitance	CT	V <sub>R</sub> = 600 V	-	17	-	pF	
Series inductance	L <sub>S</sub>	Measured lead to lead 5 mm from package body	-	8	-	nH	

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COMPLIANT

HALOGEN

FREE



www.vishay.com

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<b>DYNAMIC RECOVERY CHARACTERISTICS</b> ( $T_J = 25$ °C unless otherwise specified)								
PARAMETER	SYMBOL	TEST CO	TEST CONDITIONS			MAX.	UNITS	
		$I_F = 1.0 \text{ A}, \text{ d}I_F/\text{d}t =$	100 A/µs, V <sub>R</sub> = 30 V	-	23	-		
Boueros recoveru timo	+	$I_F = 1.0 \text{ A}, \text{ d}I_F/\text{d}t =$	50 A/µs, V <sub>R</sub> = 30 V	-	24	-	- ns	
Reverse recovery time	t <sub>rr</sub>	T <sub>J</sub> = 25 °C		-	20	-		
		T <sub>J</sub> = 125 °C		-	27	-		
Pools recovery ourrent	1	T <sub>J</sub> = 25 °C	I <sub>F</sub> = 4 A dI <sub>F</sub> /dt = 200 A/μs V <sub>B</sub> = 160 V	-	2	-	А	
Peak recovery current	I <sub>RRM</sub>	T <sub>J</sub> = 125 °C		-	3.4	-	A	
	0	$T_J = 25 \ ^{\circ}C$	VR - 100 V	-	20	-	50	
Reverse recovery charge	Q <sub>rr</sub>	T <sub>J</sub> = 125 °C		-	46	-	nC	

THERMAL - MECHANICAL SPECIFICATIONS							
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS	
Maximum junction and storage temperature range	T <sub>J</sub> , T <sub>Stg</sub>		-65	-	175	°C	
Thermal resistance, junction to case per leg	R <sub>thJC</sub>		-	2.7	3.2	°C/W	
Approximate weight				0.3		g	
				0.01		oz.	
Marking device		Case style DPAK (TO-252AA)		4EWH	02FNH		

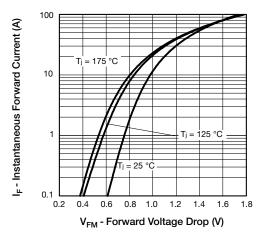


Fig. 1 - Typical Forward Voltage Drop Characteristics

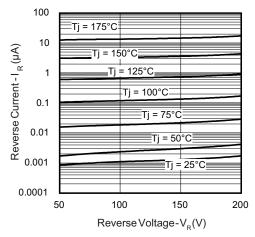


Fig. 2 - Typical Values of Reverse Current vs. Reverse Voltage

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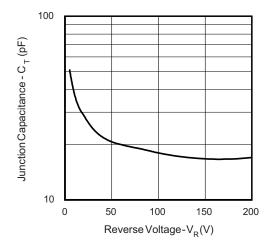
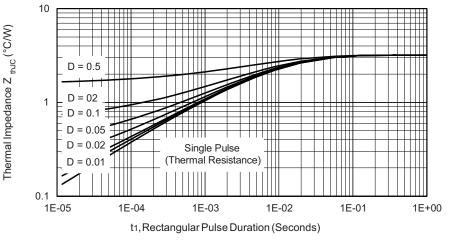
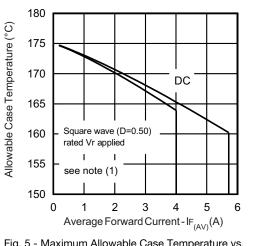
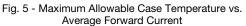


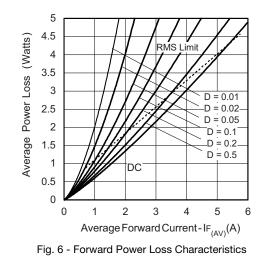
Fig. 3 - Typical Junction Capacitance vs. Reverse Voltage











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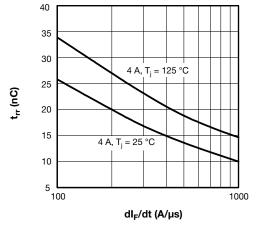


Fig. 7 - Typical Reverse Recovery Time vs. dl<sub>F</sub>/dt

#### Note

- <sup>(1)</sup> Formula used:  $T_C = T_J (Pd + Pd_{REV}) \times R_{thJC}$ ;
- $\begin{array}{l} \mathsf{Pd} = \mathsf{forward} \ \mathsf{power} \ \mathsf{loss} = \mathsf{I}_{\mathsf{F}(\mathsf{AV})} \ x \ \mathsf{V}_{\mathsf{FM}} \ \mathsf{at} \ (\mathsf{I}_{\mathsf{F}(\mathsf{AV})}/\mathsf{D}) \ (\mathsf{see} \ \mathsf{fig.} \ \mathsf{6}); \\ \mathsf{Pd}_{\mathsf{REV}} = \mathsf{inverse} \ \mathsf{power} \ \mathsf{loss} = \mathsf{V}_{\mathsf{R1}} \ x \ \mathsf{I}_{\mathsf{R}} \ (\mathsf{1} \ \mathsf{D}); \ \mathsf{I}_{\mathsf{R}} \ \mathsf{at} \ \mathsf{V}_{\mathsf{R1}} = \mathsf{rated} \ \mathsf{V}_{\mathsf{R}} \end{array}$

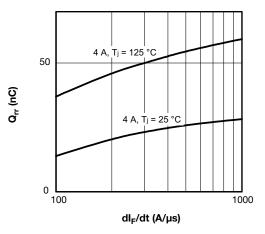


Fig. 8 - Typical Stored Charge vs. dl<sub>F</sub>/dt

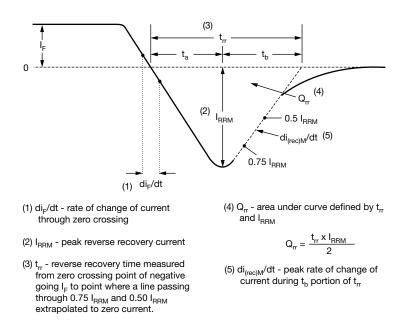


Fig. 9 - Reverse Recovery Waveform and Definitions

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**ORDERING INFORMATION TABLE** 

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SHAY

Device code	VS-	4	E	w	н	02	FN	TRL	н	М3
		2	3	4	5	6	7	8	9	10
	1 2 3	- C - C	ishay Sen urrent rati ircuit conf	ing (4 = 4 figuration	4 A)	oduct				
	4	- P	= single ( ackage id ′ = DPAK	entifier:						
	5 6 7	- V	= hyperfa oltage rati N = TO-25	ing (02 =	-	)				
	8		<ul> <li>None = tube</li> <li>TR = tape and reel</li> </ul>							
	9	•	TRL = tap TRR = ta = AEC-Q	pe and r	eel (righ		-			
	10		nvironmei 3 = halog	-		complia	nt, and	terminat	tions lea	ad (Pb)-f

ORDERING INFORMATION (Example)								
PREFERRED P/N	QUANTITY PER T/R	MINIMUM ORDER QUANTITY	PACKAGING DESCRIPTION					
VS-4EWH02FNHM3	75	3000	Antistatic plastic tube					
VS-4EWH02FNTRHM3	2000	2000	13" diameter reel					
VS-4EWH02FNTRLHM3	3000	3000	13" diameter reel					
VS-4EWH02FNTRRHM3	3000	3000	13" diameter reel					

LINKS TO RELATED DOCUMENTS					
Dimensions	www.vishay.com/doc?95519				
Part marking information	www.vishay.com/doc?95518				
Packaging information	www.vishay.com/doc?95033				
SPICE model	www.vishay.com/doc?95381				

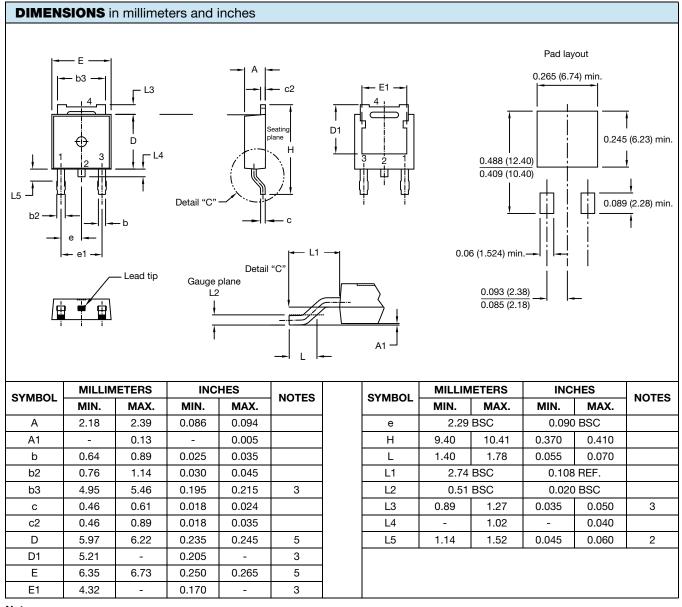
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### **Outline Dimensions**



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# DPAK (TO-252AA)



#### Notes

<sup>(1)</sup> Dimensioning and tolerancing as per ASME Y14.5M-1994

<sup>(2)</sup> Lead dimension uncontrolled in L5

<sup>(3)</sup> Dimension D1, E1, L3 and b3 establish a minimum mounting surface for thermal pad

<sup>(4)</sup> Dimensions D and E do not include mold flash. Mold flash shall not exceed 0.127 mm (0.005") per side. These dimensions are measured at the outermost extremes of the plastic body

<sup>(5)</sup> Outline conforms to JEDEC<sup>®</sup> outline TO-252AA

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